

Garam Kim

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Improvement in Self-Heating Characteristic by Incorporating Hetero-Gate-Dielectric in Gate-All-Around MOSFETs. IEEE Journal of the Electron Devices Society, 2021, 9, 36-41.	2.1	25
2	Demonstration of Fin-Tunnel Field-Effect Transistor with Elevated Drain. Micromachines, 2019, 10, 30.	2.9	19
3	High On-Current Ge-Channel Heterojunction Tunnel Field-Effect Transistor Using Direct Band-to-Band Tunneling. Micromachines, 2019, 10, 77.	2.9	18
4	F-Shaped Tunnel Field-Effect Transistor (TFET) for the Low-Power Application. Micromachines, 2019, 10, 760.	2.9	18
5	Schottky Barrier Tunnel Field-Effect Transistor using Spacer Technique. Journal of Semiconductor Technology and Science, 2014, 14, 572-578.	0.4	17
6	Analysis of Current Variation with Work Function Variation in L-Shaped Tunnel-Field Effect Transistor. Micromachines, 2020, 11, 780.	2.9	13
7	GaN-based light emitting diodes using p-type trench structure for improving internal quantum efficiency. Applied Physics Letters, 2017, 110, .	3.3	8
8	Analysis of Work-Function Variation Effects in a Tunnel Field-Effect Transistor Depending on the Device Structure. Applied Sciences (Switzerland), 2020, 10, 5378.	2.5	6
9	Improvement of self-heating effect in Ge vertically stacked GAA nanowire pMOSFET by utilizing Al ₂ O ₃ for high-performance logic device and electrical/thermal co-design. Japanese Journal of Applied Physics, 2021, 60, SCCE04.	1.5	6
10	Rigorous Study on Hump Phenomena in Surrounding Channel Nanowire (SCNW) Tunnel Field-Effect Transistor (TFET). Applied Sciences (Switzerland), 2020, 10, 3596.	2.5	5
11	Effects of Back-Gate Bias on Subthreshold Swing of Tunnel Field-Effect Transistor. Electronics (Switzerland), 2019, 8, 1415.	3.1	2
12	Surrounding Channel Nanowire Tunnel Field-Effect Transistor with Dual Gate to Reduce a Hump Phenomenon. Journal of Nanoscience and Nanotechnology, 2020, 20, 4182-4187.	0.9	2
13	Optimization of Feedback FET with Asymmetric Source Drain Doping Profile. Micromachines, 2022, 13, 508.	2.9	2
14	Optimization of spacer and source/channel junction to improve TFET characteristics. IEICE Electronics Express, 2020, 17, 20200211-20200211.	0.8	1
15	Analysis of Channel Area Fluctuation Effects of Gate-All-Around Tunnel Field-Effect Transistor. Journal of Nanoscience and Nanotechnology, 2020, 20, 4409-4413.	0.9	0